

## AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A circuit device comprising:

a first transistor including a first metal gate electrode over a first gate dielectric on a first area of a semiconductor substrate ~~and, the first metal gate electrode comprising a first metal layer~~ having a work function corresponding to the work function of ~~one of P-type silicon and N-type silicon, wherein the first metal gate electrode is one of a pure metal and a metal alloy; and~~

a second transistor complementary to the first transistor including a second metal gate electrode over a second gate dielectric on a second different area of a semiconductor substrate, the second metal gate electrode comprising a second metal layer, the second metal layer ~~and~~ having a work function corresponding to the work function of ~~the other one of P-type silicon and N-type silicon; and,~~

wherein the first metal gate electrode and the second metal gate electrode are each separately disposed in respective ones of the first area and the second area of the semiconductor substrate, and

wherein the first metal layer and second metal layer comprise the same type of metal.

2-15. (Canceled)

16. (Previously Presented) The circuit device of claim 1, wherein the first gate dielectric is silicon dioxide.

17. (Previously Presented) The circuit device of claim 1, wherein the first metal gate electrode is one of tantalum, tantalum nitride, molybdenum silicide, and molybdenum nitride.

18. (Currently Amended) A circuit device comprising:

a first transistor including a first gate electrode over a first gate dielectric on a first area of a semiconductor substrate, the first gate electrode comprising a first metal layer ~~and~~ having a Fermi

level corresponding to a work function of ~~one of P-type silicon and N-type silicon, wherein the first gate electrode is one of a pure metal and a metal alloy; and~~

a second transistor complementary to the first transistor including a second gate electrode over a second gate dielectric on a second different area of a semiconductor substrate, the second gate electrode comprising a second metal layer ~~and having a Fermi level corresponding to a work function of the other one of P-type silicon and N-type silicon; and,~~

wherein the first gate electrode and the second gate electrode are each separately disposed in respective ones of the first area and the second area of the semiconductor substrate, ~~and comprise the same type of material~~

wherein the first metal layer and second metal layer are formed from a same initial metal layer.

19. (Canceled)

20. (Previously Presented) The circuit device of claim 18, wherein the first gate dielectric is silicon dioxide.

21. (Previously Presented) The circuit device of claim 18, wherein the first gate electrode is one of tantalum, tantalum nitride, molybdenum silicide, and molybdenum nitride.